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ISSUE CLASSIFICATION	
Class	Subclass

C

PATENT DATE

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SCANNED TM Q.A. W

APPLICATION NO. 09/666156	CONT/PRIOR F	CLASS 257	SUBCLASS 335	ART UNIT 2811	EXAMINER Loke HOMAS
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Haruko Inoue
Yuichi Kitamura

High-voltage MOS transistor and method for fabricating the same

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ISSUING CLASSIFICATION															
ORIGINAL				CROSS REFERENCE(S)											
CLASS		SUBCLASS		CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)										
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